Reverse Conducting Series

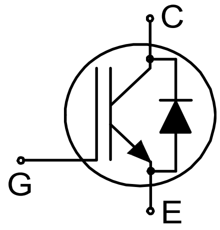
Reverse conducting IGBT with monolithic body diode

IKW30N65WR5

Data sheet

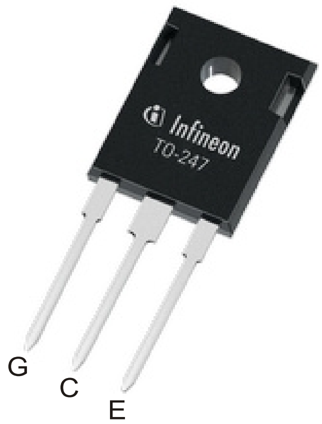
Inductrial Power Control

Reverse conducting IGBT with monolithic body diode



Features:

• Powerful monolithic diode optimized for ZCS applications
• TRENCHSTOP^{TM} 5 technology applications offers:
- high ruggedness, temperature stable behavior
- very low V_{CEsat} and low E_{off}
- easy parallel switching capability due to positive temperature coefficient in V_{CEsat}
• Low EMI
• Low electrical parameters depending (dependence) on temperature
• Qualified according to JESD-022 for target applications
• Pb-free lead plating; RoHS compliant
• Complete product spectrum and PSpice Models: http://www.infineon.com/igbt/



Applications:

• Welding
• PFC
• ZCS - converters

Key Performance and Package Parameters

Type	V_{CE}	I_C	V_{CEsat}, T_{vj}=25°C	T_{vjmax}	Marking	Package
IKW30N65WR5	650V	30A	1.4V	175°C	K30EWR5	PG-TO247-3

Table of Contents

Maximum Ratings

For optimum lifetime and reliability, Infineon recommends operating conditions that do not exceed 80% of the maximum ratings stated in this datasheet.

Parameter	Symbol	Value	Unit
Collector-emitter voltage, $T_{vj} \geq 25°C$	V_{CE}	650	V
DC collector current, limited by T_{vjmax} $T_C = 25°C$ $T_C = 117°C$	I_C	60.0 30.0	A
Pulsed collector current, t_p limited by T_{vjmax}	I_{Cpuls}	90.0	A
Turn off safe operating area $V_{CE} \leq 650V$, $T_{vj} \leq 175°C$, $t_p = 1µs$	-	90.0	A
Diode forward current, limited by T_{vjmax} $T_C = 25°C$ $T_C = 100°C$	I_F	24.0 15.0	A
Diode pulsed current, t_p limited by T_{vjmax}	I_{Fpuls}	45.0	A
Gate-emitter voltage	V_{GE}	±20	V
Power dissipation $T_C = 25°C$ Power dissipation $T_C = 117°C$	P_{tot}	185.0 75.0	W
Operating junction temperature	T_{vj}	-40...+175	°C
Storage temperature	T_{stg}	-55...+150	°C
Soldering temperature, wave soldering 1.6mm (0.063in.) from case for 10s		260	°C
Mounting torque, M3 screw Maximum of mounting processes: 3	M	0.6	Nm

Thermal Resistance

Parameter	Symbol	Conditions	Max. Value	Unit
Characteristic				
IGBT thermal resistance, junction - case	$R_{th(j-c)}$		0.81	K/W
Diode thermal resistance, junction - case	$R_{th(j-c)}$		3.40	K/W
Thermal resistance junction - ambient	$R_{th(j-a)}$		40	K/W

Electrical Characteristic, at T_{vj} = 25°C, unless otherwise specified

Parameter	Symbol	Conditions	Value min.	Value typ.	Value max.	Unit
Static Characteristic						
Collector-emitter breakdown voltage	$V_{(BR)CES}$	V_{GE} = 0V, I_C = 0.50mA	650	-	-	V
Collector-emitter saturation voltage	V_{CEsat}	V_{GE} = 15.0V, I_C = 30.0A T_{vj} = 25°C T_{vj} = 175°C	- -	1.40 1.65	1.80 -	V
Diode forward voltage	V_F	V_{GE} = 0V, I_F = 15.0A T_{vj} = 25°C T_{vj} = 175°C	- -	1.40 1.50	1.90 -	V
Gate-emitter threshold voltage	$V_{GE(th)}$	I_C = 0.30mA, V_{CE} = V_{GE}	3.2	4.0	4.8	V
Zero gate voltage collector current	I_{CES}	V_{CE} = 650V, V_{GE} = 0V T_{vj} = 25°C T_{vj} = 175°C	- -	- -	40.0 -	µA
Gate-emitter leakage current	I_{GES}	V_{CE} = 0V, V_{GE} = 20V	-	-	100	nA
Transconductance	g_{fs}	V_{CE} = 20V, I_C = 30.0A	-	35.0	-	S
Integrated gate resistor	r_G			none		Ω

Electrical Characteristic, at T_{vj} = 25°C, unless otherwise specified

Parameter	Symbol	Conditions	Value min.	Value typ.	Value max.	Unit
Dynamic Characteristic						
Input capacitance	C_{ies}	V_{CE} = 25V, V_{GE} = 0V, f = 1MHz	-	3700	-	pF
Output capacitance	C_{oes}		-	35	-	
Reverse transfer capacitance	C_{res}		-	16	-	
Gate charge	Q_G	V_{CC} = 520V, I_C = 30.0A, V_{GE} = 15V	-	155.0	-	nC
Internal emitter inductance measured 5mm (0.197 in.) from case	L_E		-	13.0	-	nH

Switching Characteristic, Inductive Load

Parameter	Symbol	Conditions	Value min.	Value typ.	Value max.	Unit
IGBT Characteristic, at T_{vj} = 25°C						
Turn-on delay time	$t_{d(on)}$	T_{vj} = 25°C, V_{CC} = 400V, I_C = 15.0A, V_{GE} = 0.0/15.0V, $R_{G(on)}$ = 26.0Ω, $R_{G(off)}$ = 26.0Ω, $L\sigma$ = 45nH, $C\sigma$ = 32pF $L\sigma$, $C\sigma$ from Fig. E Energy losses include “tail” and diode reverse recovery.	-	39	-	ns
Rise time	t_r		-	12	-	ns
Turn-off delay time	$t_{d(off)}$		-	367	-	ns
Fall time	t_f		-	9	-	ns
Turn-on energy	E_{on}		-	0.99	-	mJ
Turn-off energy	E_{off}		-	0.33	-	mJ
Total switching energy	E_{ts}		-	1.32	-	mJ

Diode Characteristic, at T_{vj} = 25°C

Diode reverse recovery time	t_{rr}	T_{vj} = 25°C, V_R = 400V, I_F = 15.0A, di_F/dt = 900A/µs	-	95	-	ns
Diode reverse recovery charge	Q_{rr}		-	1.25	-	µC
Diode peak reverse recovery current	I_{rrm}		-	22.0	-	A
Diode peak rate of fall of reverse recovery current during t_b	di_{rr}/dt		-	-590	-	A/µs

Switching Characteristic, Inductive Load

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	
IGBT Characteristic, at T_{vj} = 175°C						
Turn-on delay time	$t_{d(on)}$	T_{vj} = 175°C, V_{CC} = 400V, I_C = 15.0A, V_{GE} = 0.0/15.0V, $R_{G(on)}$ = 26.0Ω, $R_{G(off)}$ = 26.0Ω, $L\sigma$ = 45nH, $C\sigma$ = 32pF $L\sigma$, $C\sigma$ from Fig. E Energy losses include “tail” and diode reverse recovery.	-	35	-	ns
Rise time	t_r		-	14	-	ns
Turn-off delay time	$t_{d(off)}$		-	423	-	ns
Fall time	t_f		-	6	-	ns
Turn-on energy	E_{on}		-	1.09	-	mJ
Turn-off energy	E_{off}		-	0.46	-	mJ
Total switching energy	E_{ts}		-	1.55	-	mJ

Diode Characteristic, at T_{vj} = 175°C

Diode reverse recovery time	t_{rr}	T_{vj} = 175°C, V_R = 400V, I_F = 15.0A, di_F/dt = 900A/µs	-	121	-	ns
Diode reverse recovery charge	Q_{rr}		-	2.15	-	µC
Diode peak reverse recovery current	I_{rrm}		-	28.0	-	A
Diode peak rate of fall of reverse recovery current during t_b	di_{rr}/dt		-	-1100	-	A/µs

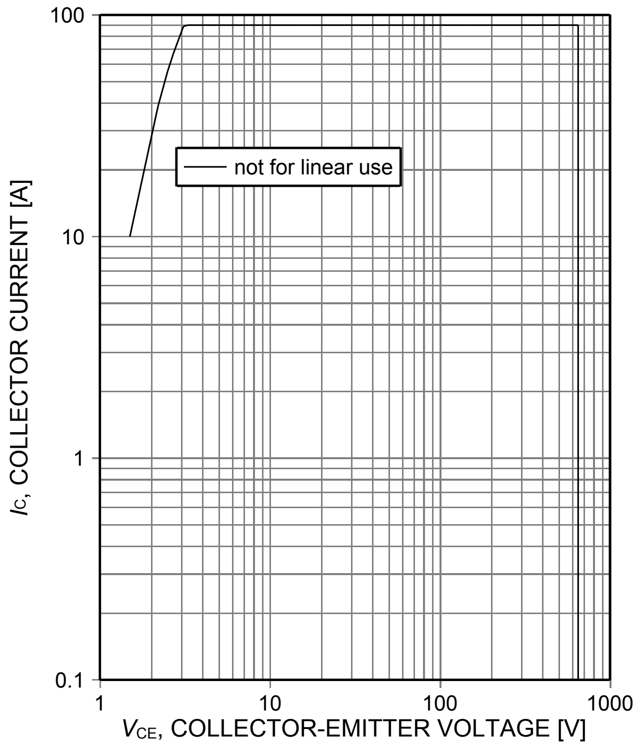


Figure 1. **Forward bias safe operating area**
(D=0, T_C=25°C, T_{vj}≤175°C, V_{GE}=15V, t_p=1µs)

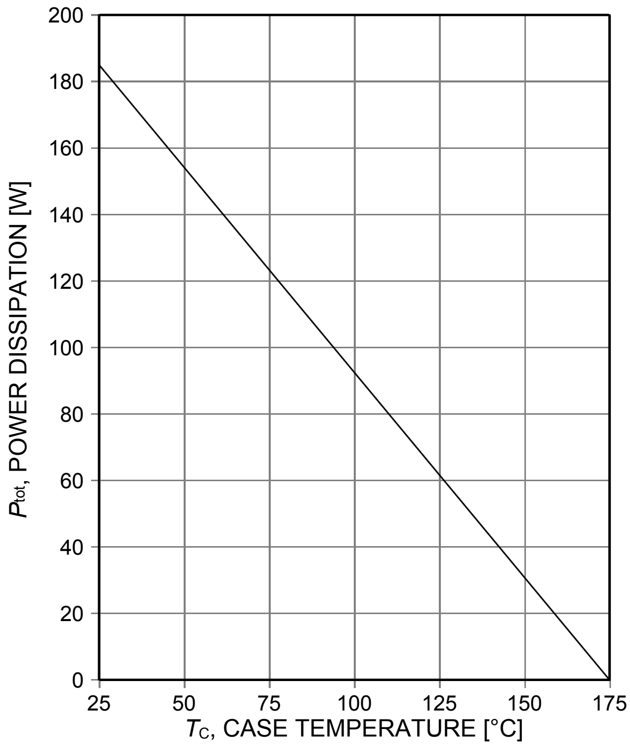


Figure 2. **Power dissipation as a function of case temperature**
(T_{vj}≤175°C)

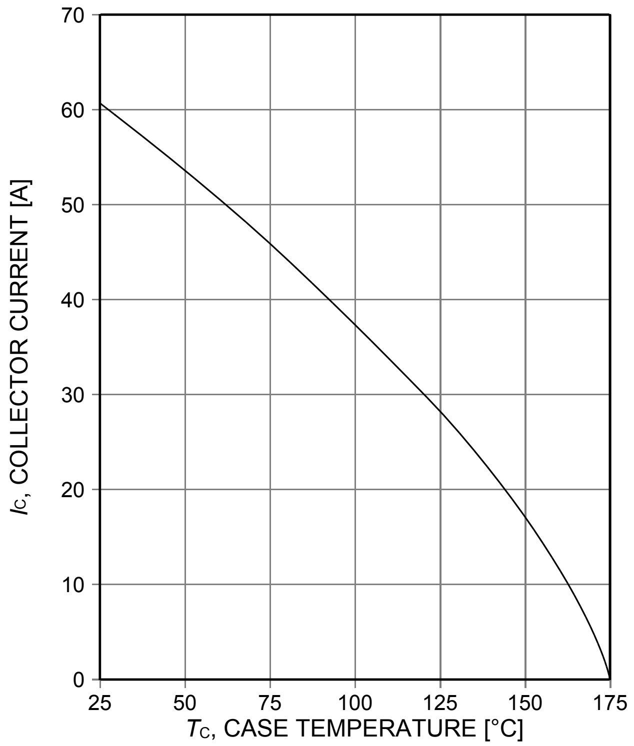


Figure 3. **Collector current as a function of case temperature**
(V_{GE}≥15V, T_{vj}≤175°C)

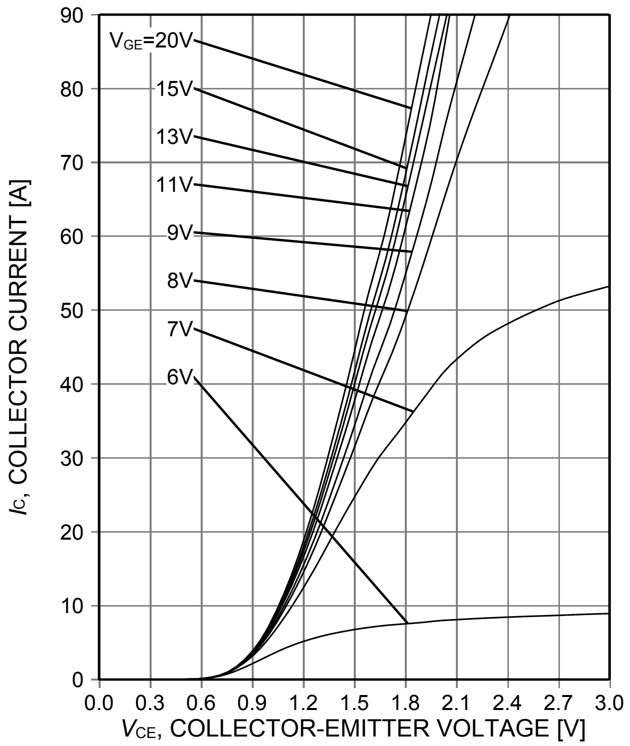


Figure 4. **Typical output characteristic**
(T_{vj}=25°C)

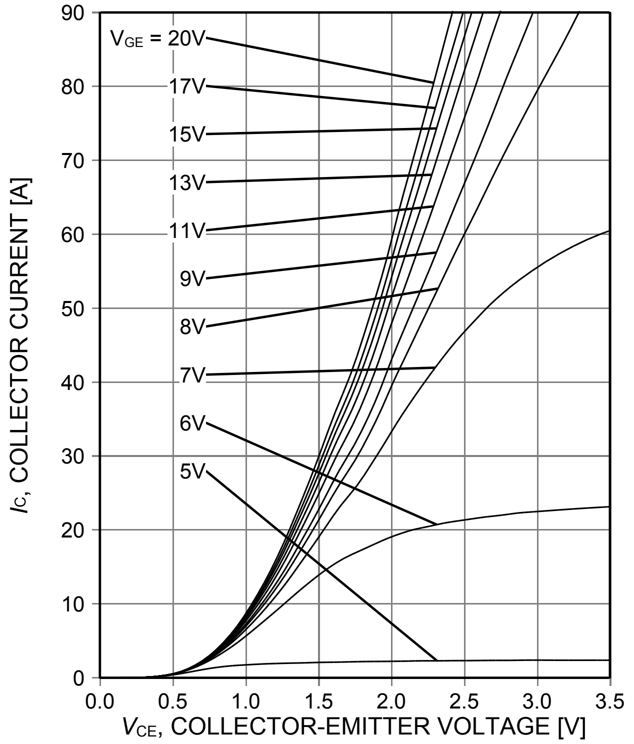


Figure 5. **Typical output characteristic**
(T_{vj}=175°C)

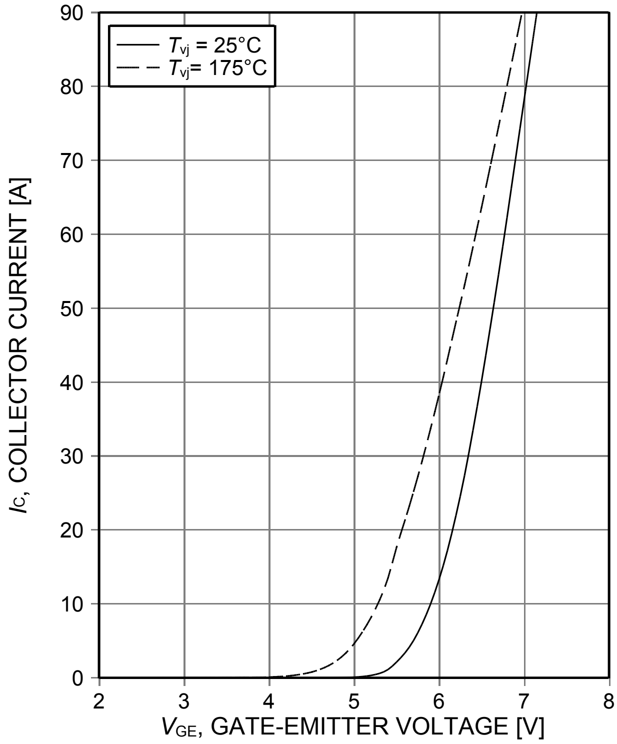


Figure 6. **Typical transfer characteristic**
(V_{CE}=20V)

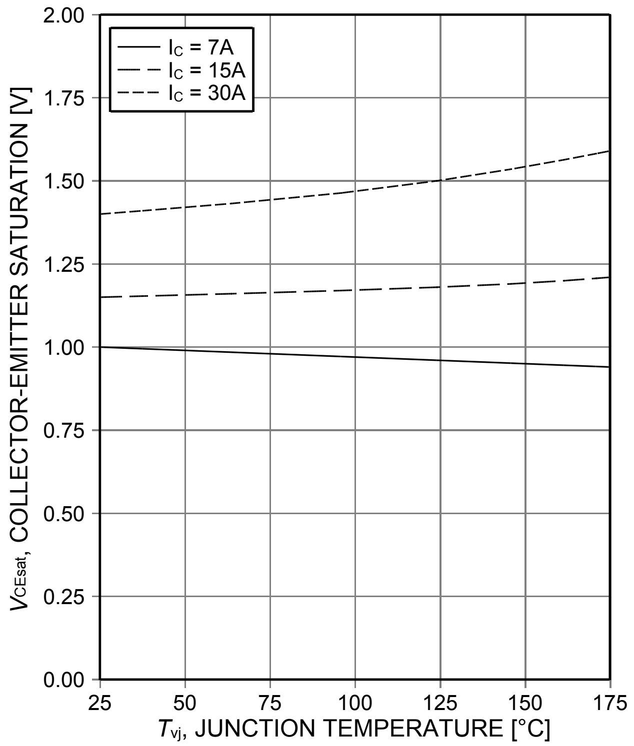


Figure 7. **Typical collector-emitter saturation voltage as a function of junction temperature**
(V_{GE}=15V)

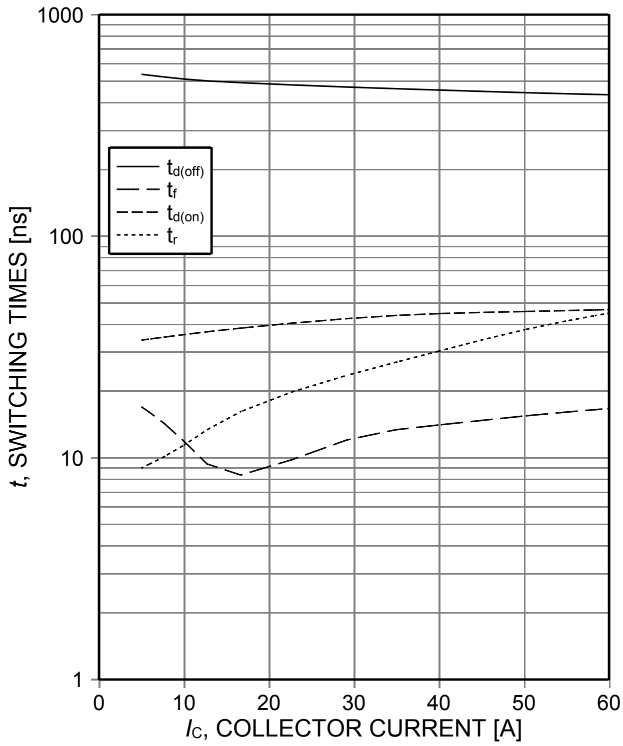


Figure 8. **Typical switching times as a function of collector current**
(inductive load, T_{vj}=175°C, V_{CE}=400V, V_{GE}=0/15V, $R_{G(on)}$=26Ω, $R_{G(off)}$=26Ω, dynamic test circuit in Figure E)

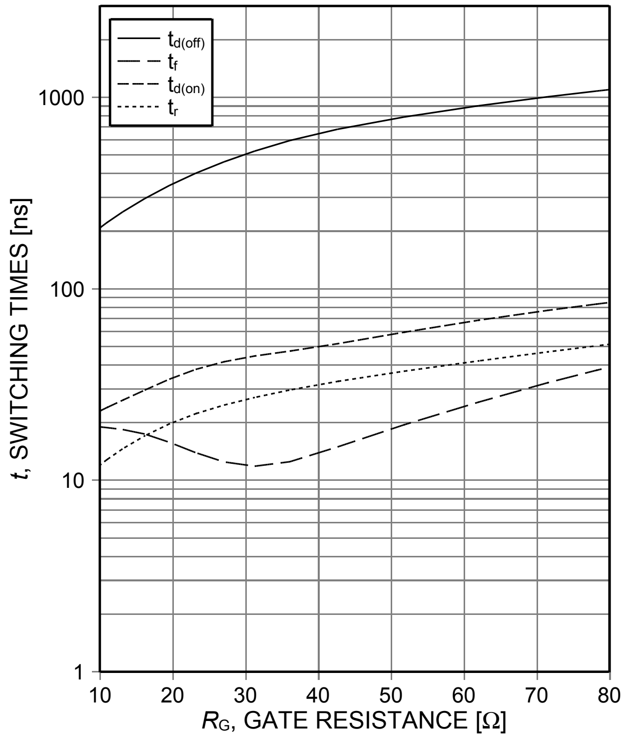


Figure 9. **Typical switching times as a function of gate resistance**
(inductive load, T_{vj}=175°C, V_{CE}=400V, V_{GE}=0/15/V, I_C=30A, dynamic test circuit in Figure E)

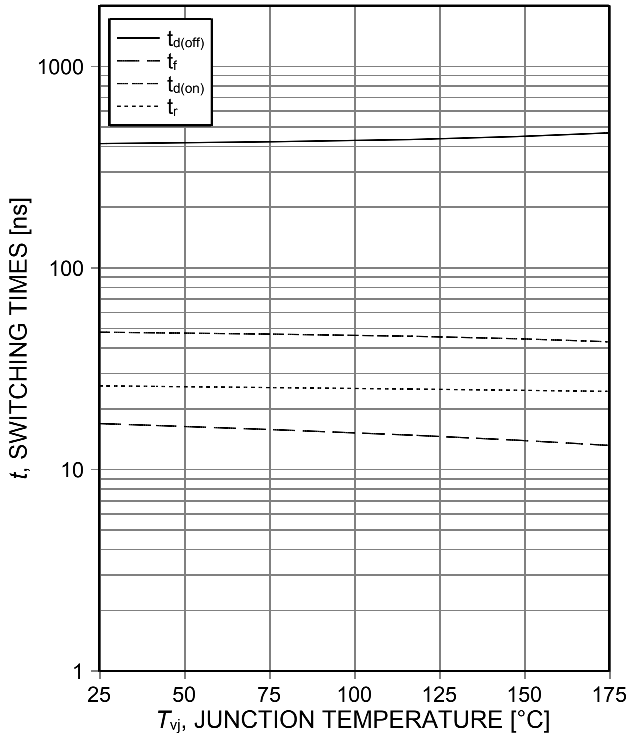


Figure 10. **Typical switching times as a function of junction temperature**
(inductive load, V_{CE}=400V, V_{GE}=0/15V, I_C=30A, $R_{G(on)}$=26Ω, $R_{G(off)}$=26Ω, dynamic test circuit in Figure E)

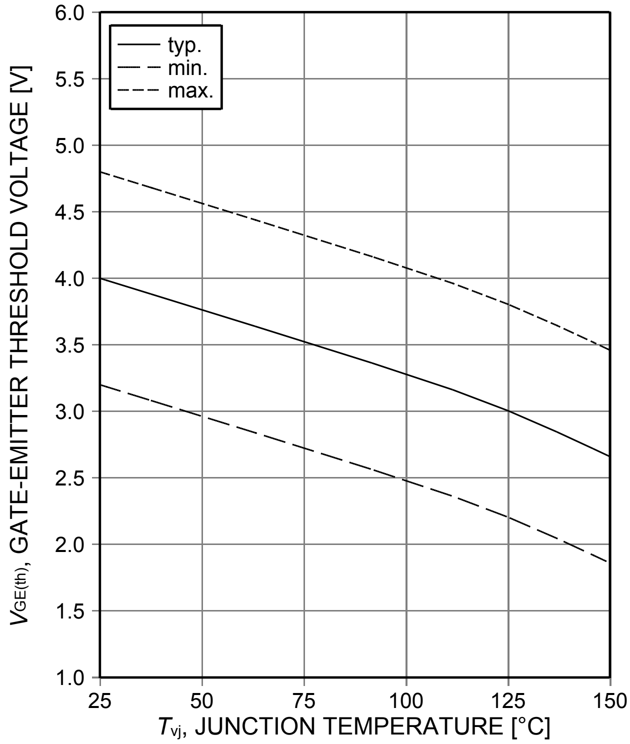


Figure 11. **Gate-emitter threshold voltage as a function of junction temperature**
(I_C=0.3mA)

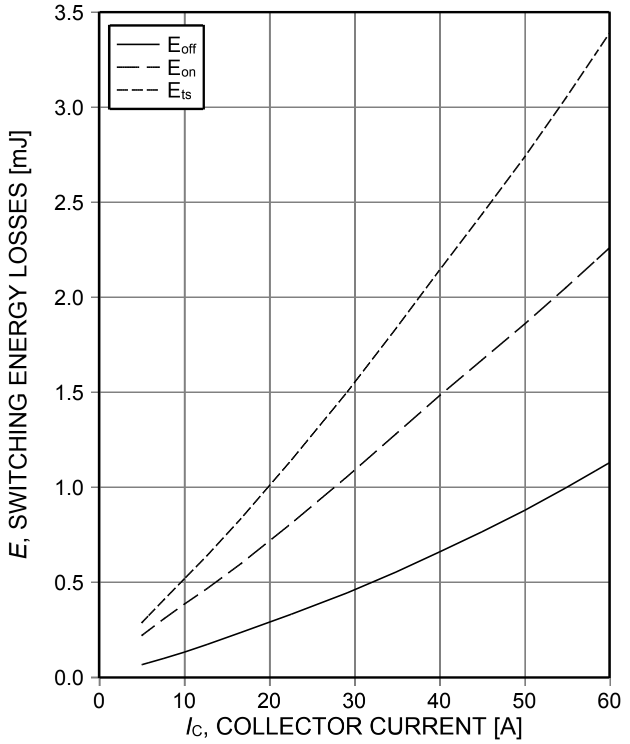


Figure 12. **Typical switching energy losses as a function of collector current**
(inductive load, T_{vj}=175°C, V_{CE}=400V, V_{GE}=0/15V, $R_{G(on)}$=26Ω, $R_{G(off)}$=26Ω, dynamic test circuit in Figure E)

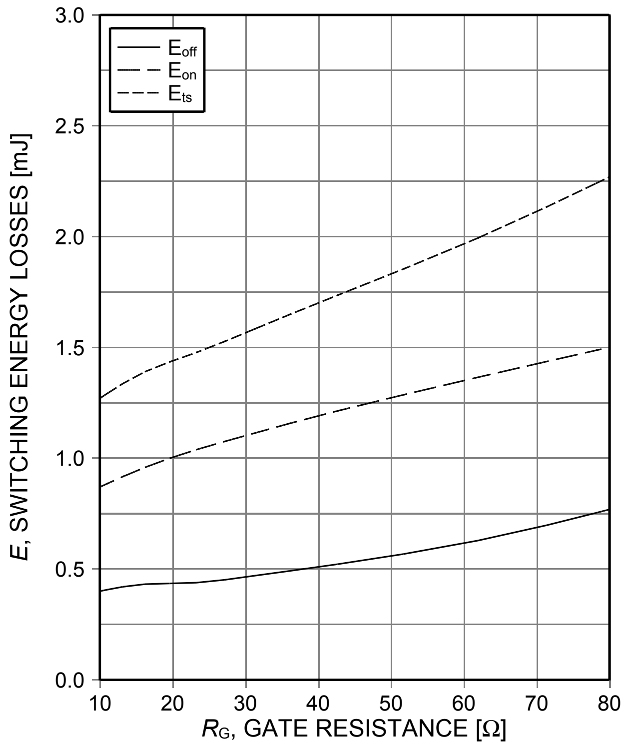


Figure 13. **Typical switching energy losses as a function of gate resistance**
(inductive load, T_{vj}=175°C, V_{CE}=400V, V_{GE}=0/15V, I_C=30A, dynamic test circuit in Figure E)

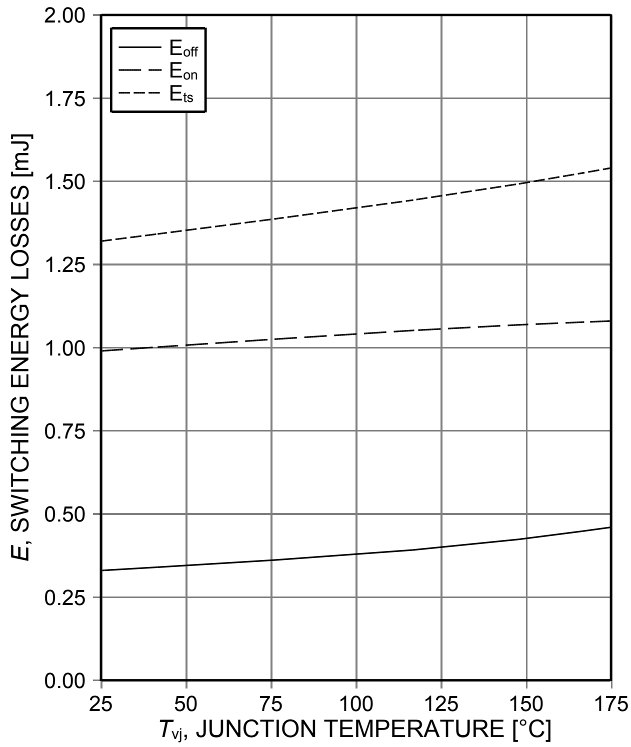


Figure 14. **Typical switching energy losses as a function of junction temperature**
(inductive load, V_{CE}=400V, V_{GE}=0/15V, I_C=30A, $R_{G(on)}$=26Ω, $R_{G(off)}$=26Ω, dynamic test circuit in Figure E)

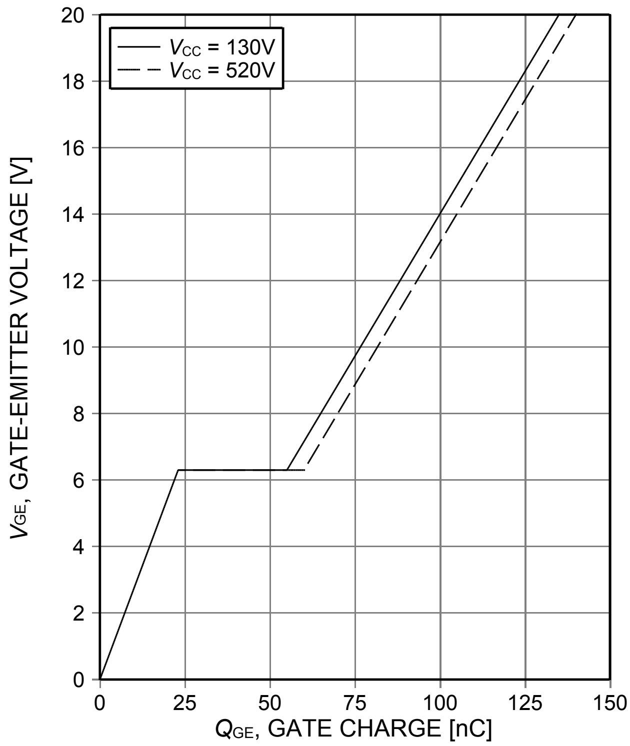


Figure 15. **Typical gate charge**
(I_C=30A)

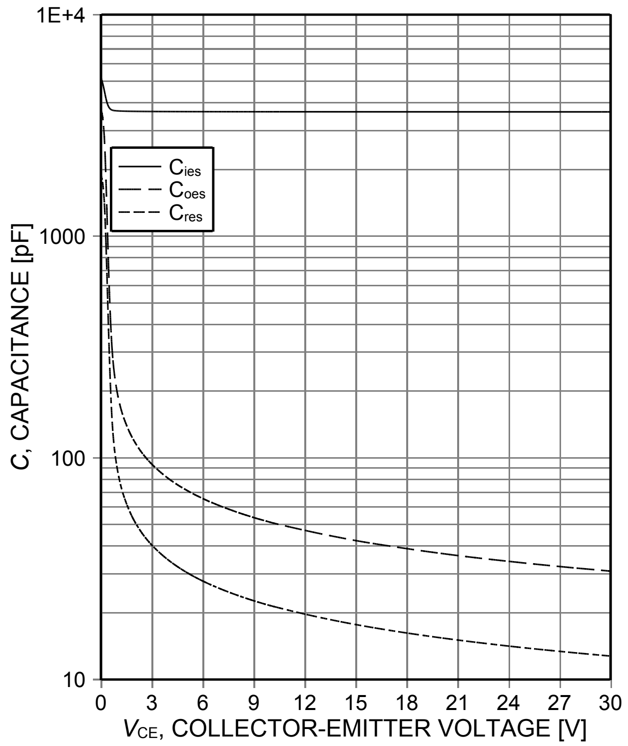


Figure 16. **Typical capacitance as a function of collector-emitter voltage**
(V_{GE}=0V, f=1MHz)

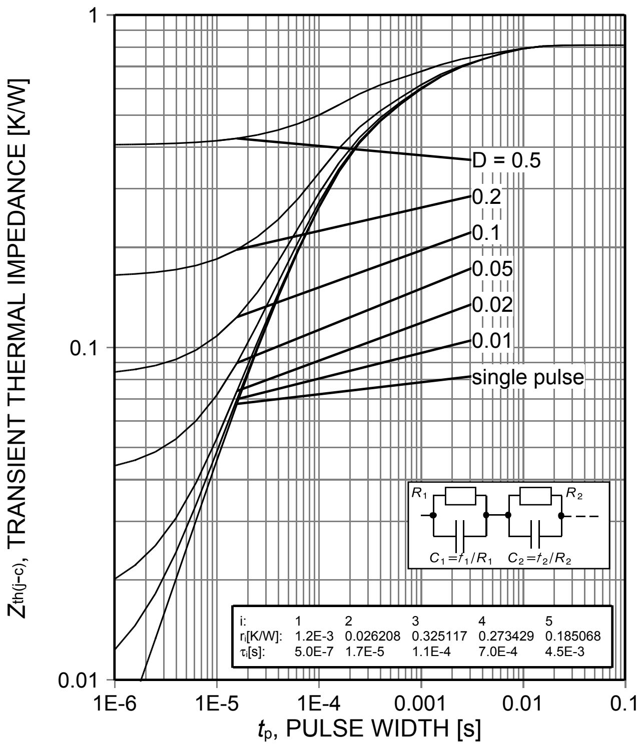


Figure 17. **IGBT transient thermal impedance**
($D=t_p/T$)

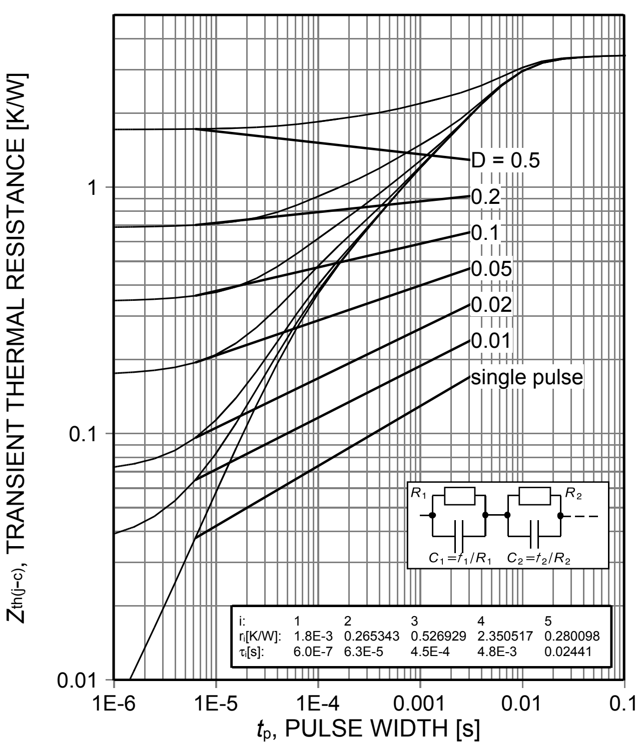


Figure 18. **Diode transient thermal impedance as a function of pulse width**
($D=t_p/T$)

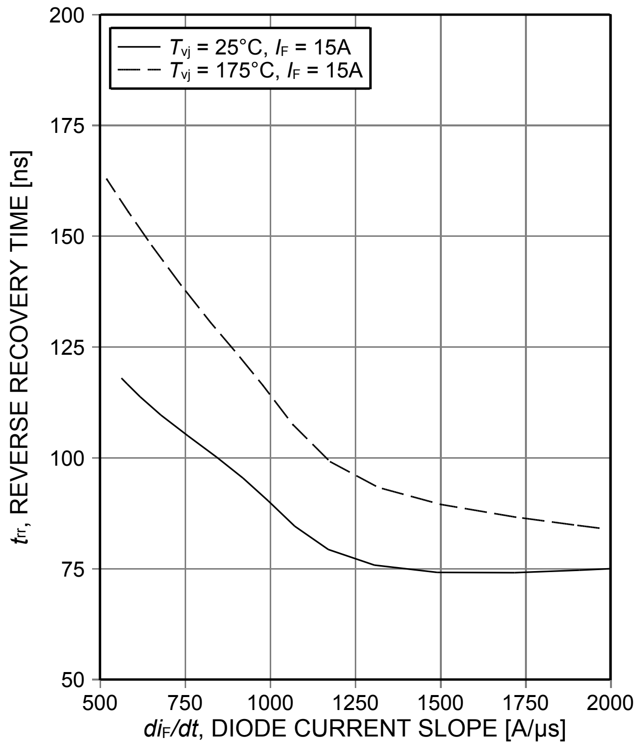


Figure 19. **Typical reverse recovery time as a function of diode current slope**
(V_R=400V)

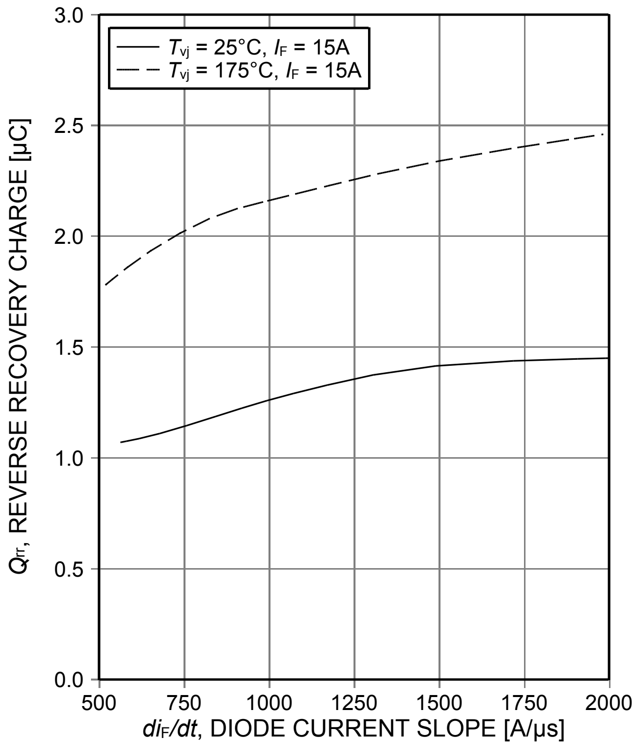


Figure 20. **Typical reverse recovery charge as a function of diode current slope**
(V_R=400V)

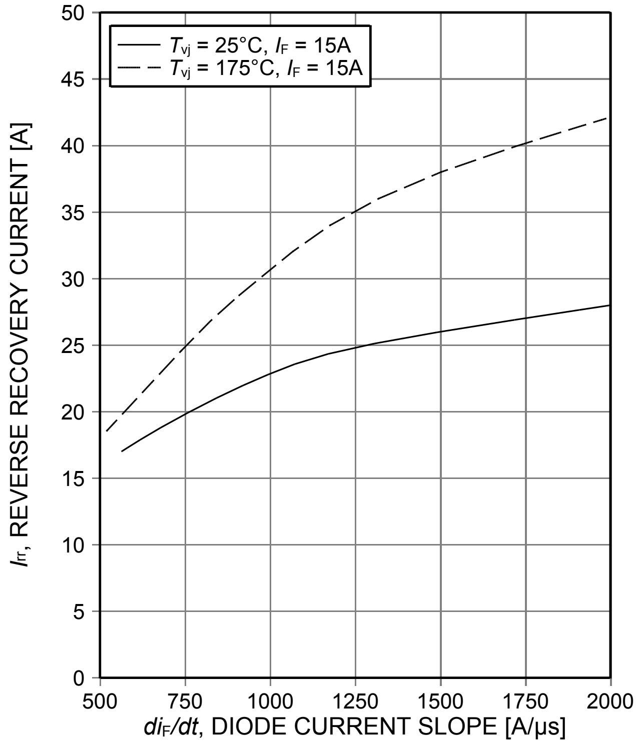


Figure 21. **Typical reverse recovery current as a function of diode current slope**
(V_R=400V)

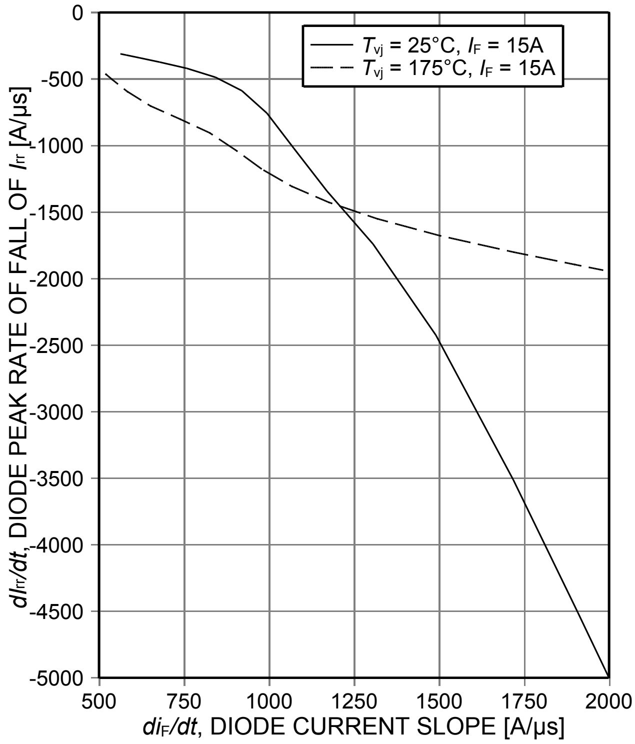


Figure 22. **Typical diode peak rate of fall of reverse recovery current as a function of diode current slope**
(V_R=400V)

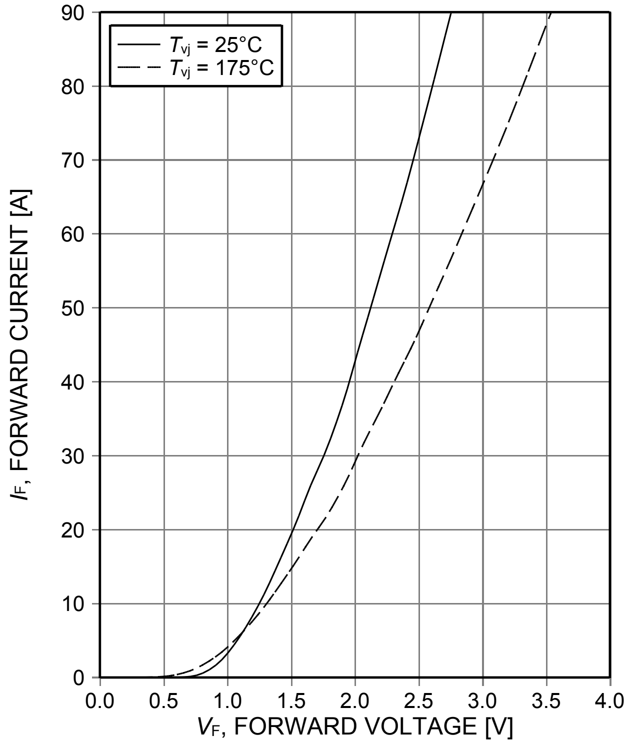


Figure 23. **Typical diode forward current as a function of forward voltage**

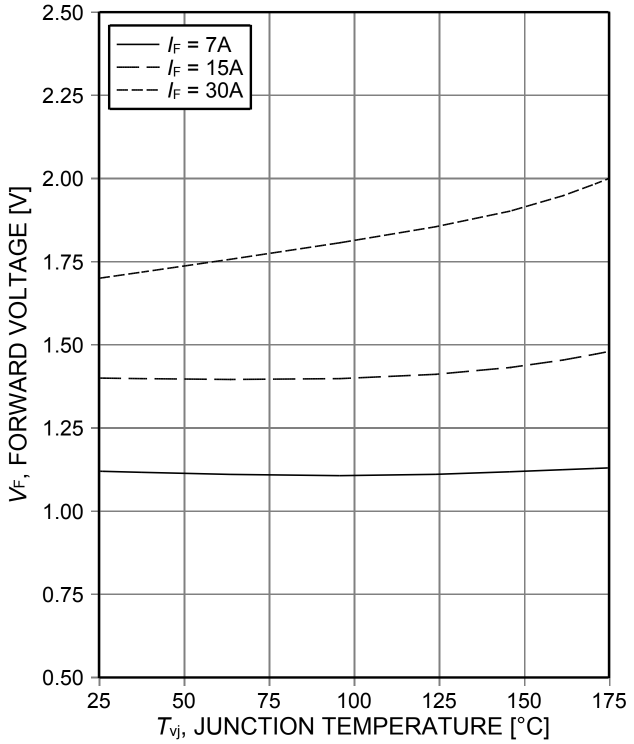
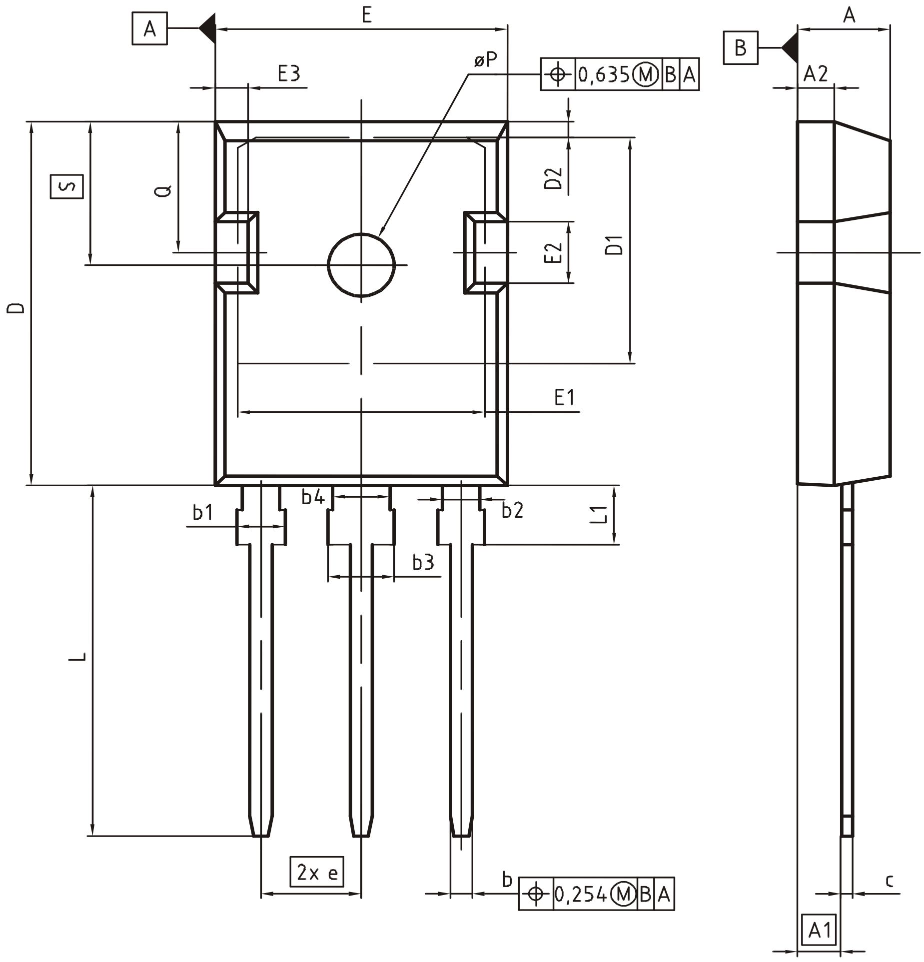


Figure 24. **Typical diode forward voltage as a function of junction temperature**

Package Drawing PG-TO247-3

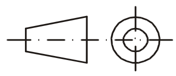


DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	4.83	5.21	0.190	0.205
A1	2.27	2.54	0.089	0.100
A2	1.85	2.16	0.073	0.085
b	1.07	1.33	0.042	0.052
b1	1.90	2.41	0.075	0.095
b2	1.90	2.16	0.075	0.085
b3	2.87	3.38	0.113	0.133
b4	2.87	3.13	0.113	0.123
c	0.55	0.68	0.022	0.027
D	20.80	21.10	0.819	0.831
D1	16.25	17.65	0.640	0.695
D2	0.95	1.35	0.037	0.053
E	15.70	16.13	0.618	0.635
E1	13.10	14.15	0.516	0.557
E2	3.68	5.10	0.145	0.201
E3	1.00	2.60	0.039	0.102
e	5.44 (BSC)		0.214 (BSC)	
N	3		3	
L	19.80	20.32	0.780	0.800
L1	4.10	4.47	0.161	0.176
øP	3.50	3.70	0.138	0.146
Q	5.49	6.00	0.216	0.236
S	6.04	6.30	0.238	0.248

DOCUMENT NO.
Z8B00003327

SCALE 0 5 0 5 7.5mm

EUROPEAN PROJECTION



ISSUE DATE
09-07-2010

REVISION
05

Testing Conditions

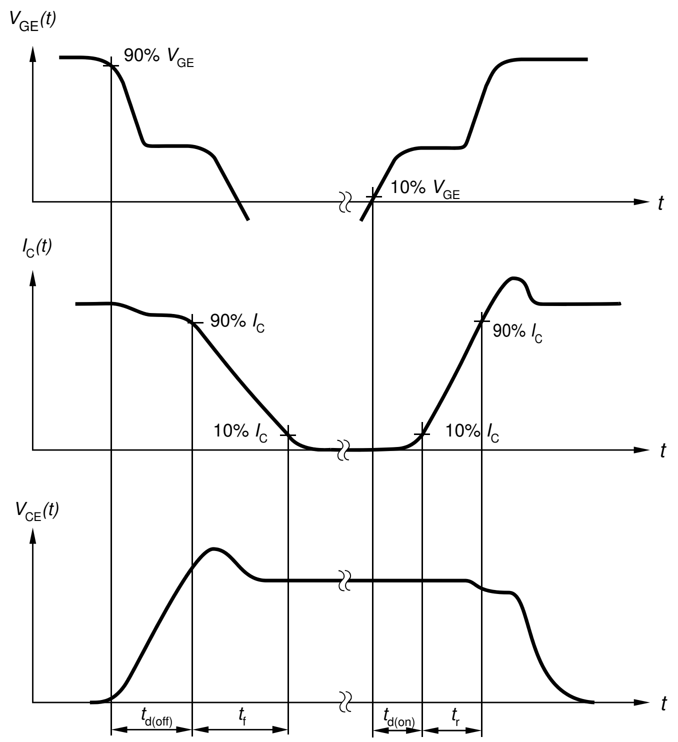


Figure A. **Definition of switching times**

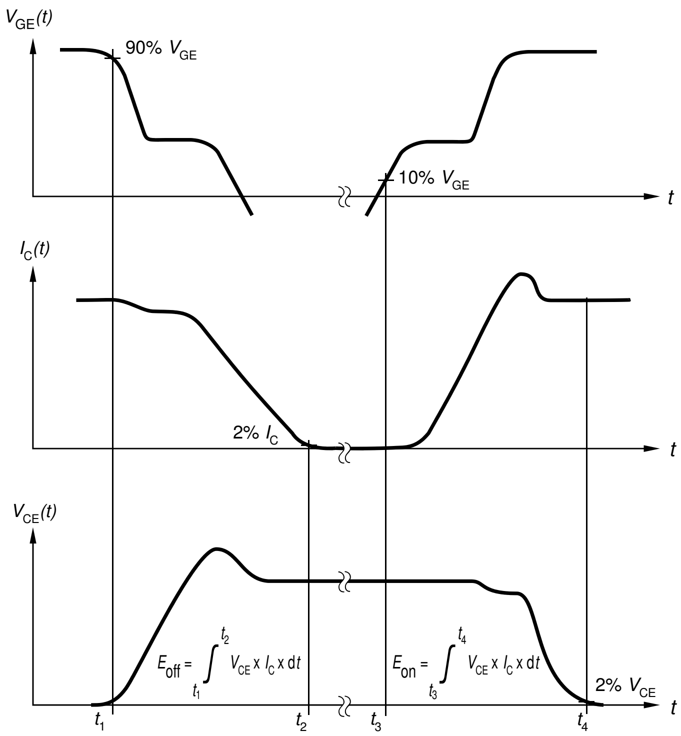


Figure B. **Definition of switching losses**

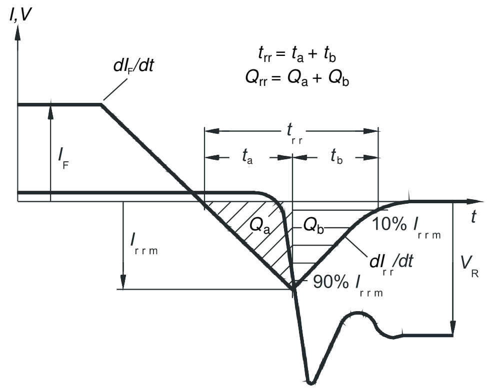


Figure C. **Definition of diode switching characteristics**

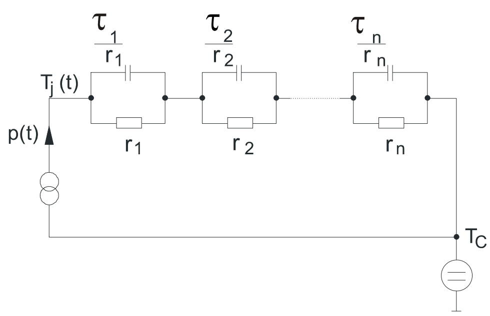


Figure D. **Thermal equivalent circuit**

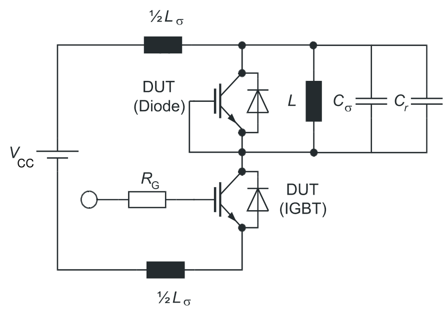


Figure E. **Dynamic test circuit**
Parasitic inductance L_{σ},
parasitic capacitor C_{σ},
relief capacitor C_r,
(only for ZVT switching)

Revision History

IKW30N65WR5

Revision: 2015-06-01, Rev. 1.3

Previous Revision

Revision	Date	Subjects (major changes since last revision)
1.1	2015-04-23	Preliminary data sheet
1.2	2015-05-12	Minor change Figure 3
1.3	2015-06-01	Update Figure 14 E(T)

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